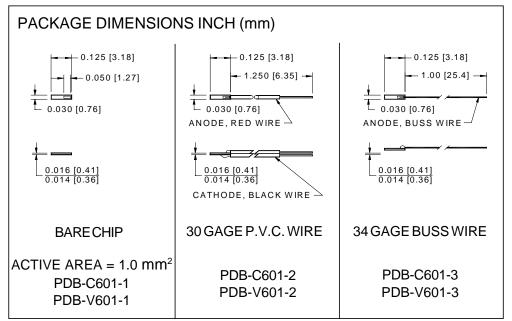
## PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C601 Photovoltaic Type PDB-V601





## **FEATURES**

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

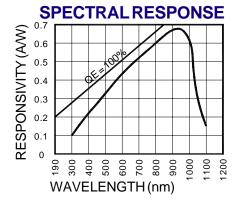
**DESCRIPTION:** Low cost blue enhanced planar diffused silicon solderable photodiode. The **PDB-V601** cell is designed for low noise, photovoltaic applications. The **PDB-C601** cell is designed for low capacitance, high speed, photoconductive operation. They are available bare, PVC or buss wire leads.

## **APPLICATIONS**

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

## ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER .	PDB-	C601	PDB-	V601	UNITS	
• · · · · · · ·	1740 4012121		MAX	MIN	MAX	010	
V <sub>BR</sub>	Reverse Voltage		75		25	V	
T <sub>STG</sub>	Storage Temperature	-40	+125	-40	+125	∘C	
То	Operating Temperature Range	-40	+100	-40	+100	∘C	
Ts	Soldering Temperature		+224		+224	°C	
I <sub>L</sub>	Light Current		500		500	mA	



**ELECTRO-OPTICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	PDB-C601			PDB-V601			LINUTO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	15	17		10	13		$\mu$ A
ΙD	Dark Current	H = 0, V <sub>R</sub> = 5 V*		.5	2		3	7	nA
Rsh	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	60	150		100	250		MΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8			-8		%/°C
С	Junction Capacitance	H = 0, V <sub>R</sub> = 5 V**		10			250		pF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	25	50		5	15		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 0 V @ Peak	1 x 10 <sup>-14</sup> TYP		2 x 10 <sup>-14</sup> TYP			W/ √Hz	
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 5 V**		10			300		nS

<sup>\*</sup>VR = 100 mV on Photovoltaic type

<sup>\*\*</sup>VR = 0 V on Photovoltaic type